

APPLICATION NO. 10/001421

YR

CLMPTO

September 20, 2004

1.-10. (Cancelled)

11. (Currently Amended) An intermediate interconnect structure for a semiconductor chip comprising:

~~nonreflowed~~ an intermediate solder assembly including :

a Pb-rich ball attached to said semiconductor chip and having an exposedouter surface;

and

a thin cap layer of Sn on said exposedouter surface of said Pb-rich ball;

said Sn layer having a thickness of less than 10.2 μ m (0.4 mils) and having a melting temperature lower than that of Pb, thereby said intermediate interconnect structure adapted so that Sn from said thin layer and Pb from said ball are diffused and intermixed after reflowing and annealing to form ~~an~~ a solder assembly .

12.-14. (Cancelled)

CLAIMS 15-19 (CANCELLED)